



THW 2826

CERTIFICATE OF MAILING UNDER 37 C.F.R. §1.8

I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail, with sufficient postage, in an envelope addressed to: Commissioner for Patents, P. O. Box 1450, Alexandria, VA 22313-1450, on the below date:

Date: February 24, 2006 Name: Terry Wand Signature: Terry Wand

**BRINKS
HOFFER
GILSON
& LIONE**

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Appln. of: **Ko, et al.**

Appln. No.: **10/502,110**

Filed: **July 21, 2004**

For: **PLANAR AVALANCHE
PHOTODIODE**

Attorney Docket No: **10555-085**

Examiner:

Art Unit: **2826**

Mail Stop Amendment
Commissioner for Patents
P. O. Box 1450
Alexandria, VA 22313-1450

TRANSMITTAL

Sir:

Attached is/are:

- ☒ Second Supplemental Information Disclosure Statement and 1 Sheet of Form PTO-1449, and 5 required references
- ☒ Return Receipt Postcard

Fee calculation:

- ☒ No additional fee is required.
- ☐ Small Entity.
- ☐ An extension fee in an amount of \$_____ for a _____-month extension of time under 37 C.F.R. § 1.136(a).
- ☐ A petition or processing fee in an amount of \$_____ under 37 C.F.R. § 1.17(_____).
- ☐ An additional filing fee has been calculated as shown below:

					Small Entity			Not a Small Entity	
	Claims Remaining After Amendment		Highest No. Previously Paid For	Present Extra	Rate	Add'l Fee	or	Rate	Add'l Fee
Total		Minus			x \$9=			x \$18=	
Indep.		Minus			x 43=			x \$86=	
First Presentation of Multiple Dep. Claim					+\$145=			+\$290=	
					Total	\$		Total	\$

Fee payment:

- ☐ A check in the amount of \$_____ to cover the above-identified fee(s) is enclosed.
- ☐ Please charge Deposit Account No. 23-1925 in the amount of \$_____. A copy of this Transmittal is enclosed for this purpose.
- ☐ Payment by credit card in the amount of \$_____ (Form PTO-2038 is attached).
- ☒ The Director is hereby authorized to charge payment of any additional filing fees required under 37 CFR § 1.16 and any patent application processing fees under 37 CFR § 1.17 associated with this paper (including any extension fee required to ensure that this paper is timely filed), or to credit any overpayment, to Deposit Account No. 23-1925.

Respectfully submitted,

February 24, 2006
Date

John M. Card (Reg. No. 48,423)



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Appln. of: KO ET AL.

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SECOND SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

In accordance with the duty of disclosure under 37 C.F.R. §1.56 and §§1.97-1.98, and more particularly in accordance with 37 C.F.R. §1.97(b), Applicants hereby cite the following reference(s):

No.	Date of Publication	Patentee/Applicant/Assignee
6,104,047	08/2000	Watanabe
6,635,908	10/2003	Tanaka, et al.
M.A. Itzler, C.S. Wang, S. McCoy, N. Codd and N. Komba, Planar bulk InP avalanche photodiode design for 2.5 and 10Gb/s applications, Proc 24th ECOC 1998, paper MoB03		
L.E. Tarof, J. Yu, R. Bruce, D.G. Knight, T. Baird and B. Oosterbrink, High frequency performance of separate absorption grading charge and multiplication InP/InGaAs avalanche photodiodes, IEEE Photon. Technol. Lett. 5, 672-674, 1993		
Watanabe, T. Nakata, M. Tsuji, K. Makita, K. Taguchi, High reliability and low dark current 10 Gb/s planar superlattice avalanche photodiodes, IEEE Photon. Technol. Lett. 9, 1619-1621, 1997		
J.C. Campbell, S. Demiquel, F. Ma, A. Beck, X. Guo, S. Wang, X. Zeng, X. Li, J.D. Beck, M.A. Kinch, A. Huntington, L.A. Coldren, J. Decobert, N. Tscherpner, Recent advances in avalanche photodiodes, IEEE J. Select. Topics Quantum Electron., 10, 777-787, 2004		
R.R. Sutherland, C.P. Skrimshire, M.J. Robertson, A reliability methodology applied to very high reliability planar InGaAs/InP PIN photodetectors, Br. Telecom. Technol. J., 7, 69-77, Jan. 1989		

Applicants are enclosing Form PTO-1449 (one sheet), along with a copy of each listed reference for which a copy is required under 37 C.F.R. §1.98(a)(2). As each of the listed references is in English, no further commentary is believed to be necessary,

37 C.F.R §1.98(a)(3). Applicants respectfully request the Examiner's consideration of the above reference(s) and entry thereof into the record of this application.

By submitting this Statement, Applicants are attempting to fully comply with the duty of candor and good faith mandated by 37 C.F.R. §1.56. As such, this Statement is not intended to constitute an admission that any of the enclosed references, or other information referred to therein, constitutes "prior art" or is otherwise "material to patentability," as that phrase is defined in 37 C.F.R. §1.56(a).

Applicants have calculated no fee to be due in connection with the filing of this Statement. However, the Director is authorized to charge any fee deficiency associated with the filing of this Statement to a deposit account, as authorized in the Transmittal accompanying this Statement.

Respectfully submitted,

2/24/06
Date



John M. Card (Reg. No.48,423)

FORM PTO-1449	APPLICATION NO. 10/502,110	CASE NO. 10555-085
LIST OF PATENTS AND PUBLICATIONS FOR APPLICANT'S INFORMATION DISCLOSURE STATEMENT	FILING DATE July 21, 2004	ART UNIT 2826
APPLICANT(S): Ko, et al.		

REFERENCE DESIGNATION

U.S. PATENT DOCUMENTS

[illegible]

FOREIGN PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	COUNTRY	CLASS/ SUBCLASS	TRANSLATION	
						YES	NO

EXAMINER INITIAL	OTHER ART (Including Author, Title, Date, Pertinent Pages, etc.)	
		M.A. Itzler, C.S. Wang, S. McCoy, N. Codd and N. Komba, Planar bulk InP avalanche photodiode design for 2.5 and 10Gb/s applications, Proc 24th ECOC 1998, paper MoB03
		L.E. Tarof, J. Yu, R. Bruce, D.G. Knight, T. Baird and B. Oosterbrink, High frequency performance of separate absorption grading charge and multiplication InP/InGaAs avalanche photodiodes, IEEE Photon. Technol. Lett. 5, 672-674, 1993
		Watanabe, T. Nakata, M. Tsuji, K. Makita, K. Taguchi, High reliability and low dark current 10 Gb/s planar superlattice avalanche photodiodes, IEEE Photon. Technol. Lett. 9, 1619-1621, 1997
		J.C. Campbell, S. Demiquel, F. Ma, A. Beck, X. Guo, S. Wang, X. Zeng, X. Li, J.D. Beck, M.A. Kinch, A. Huntington, L.A. Coldren, J. Decobert, N. Tscherptner, Recent advances in avalanche photodiodes, IEEE J. Select. Topics Quantum Electron., 10, 777-787, 2004
		R.R. Sutherland, C.P. Skrimshire, M.J. Robertson, A reliability methodology applied to very high reliability planar InGaAs/InP PIN photodetectors, Br. Telecom. Technol. J., 7, 69-77, Jan. 1989

EXAMINER	DATE CONSIDERED
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EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.